

KSB13003H KSC13003H / KSU13003H

NPN Silicon Power Transistor, VCBO= 900V, VCEO= 530V, IC= 1.5A

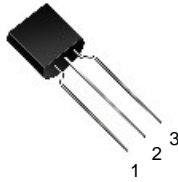
General Description

- High voltage, High speed power switching
- Suitable for Electronic Ballast up to 21W

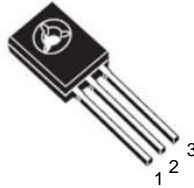
Features

- VCBO = 900V
- VCEO = 530V
- VBEO = 9V
- IC = 1.5A

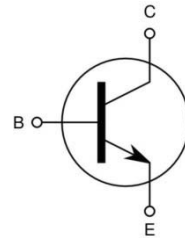
TO-92



TO-126



TO-251



Ordering Information

Ordering number	Package	Pin Assignment			Packing
		1	2	3	
KSB13003H	TO-92	B	C	E	Ammo
KSB13003HR	TO-92	E	C	B	Ammo
KSC13003H	TO-126	B	C	E	Bulk
KSU13003H	TO-251	B	C	E	Tube

KSB13003H KSC13003H / KSU13003H

NPN Silicon Power Transistor, V_{CBO}= 900V, V_{CEO}= 530V, I_C= 1.5A

Absolute Maximum Ratings TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING			UNIT
		TO-92	TO-126	TO-251	
Collector-Base Voltage	V _{CBO}	900			V
Collector-Emitter Voltage	V _{CEO}	530			V
Emitter-Base Voltage	V _{EBO}	9			V
Collector Current(DC)	I _C	1.5			A
Collector Current(Pulse)	I _{CP}	3			A
Base Current	I _B	0.75			A
Collector Dissipation(Tc=25°C)	P _C	1.1	20	25	W
Junction Temperature	T _J	150			°C
Storage Temperature	T _{STG}	-65~150			°C

Electrical Characteristics TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	V _{CBO}	I _C =500μA, I _E =0	900			V
Collector-Emitter Breakdown Voltage	V _{CEO}	I _C =10mA, I _B =0	530			V
Emitter Cut-off Current	I _{EBO}	V _{EB} =9V, I _C =0			1	mA
*DC Current Gain	h _{FE1} h _{FE2} h _{FE3}	V _{CE} =10V, I _C =1mA V _{CE} =10V, I _C =0.4A V _{CE} =10V, I _C =1A	15 20 6		40	
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1.0A, I _B =0.25A			1.0	V
*Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1.0A, I _B =0.25A			1.5	V
Output Capacitance	C _{ob}	V _{CB} =10V, f=0.1MHz		21		pF
Current Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =0.1A	4			MHz
Turn on Time	t _{on}	V _{CC} =125V, I _C =2A I _{B1} =0.2A, I _{B2} = -0.2A R _L =125Ω			1.1	μs
Storage Time	t _{stg}				4.0	μs
Fall Time	t _F				0.7	μs

* Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Characteristics

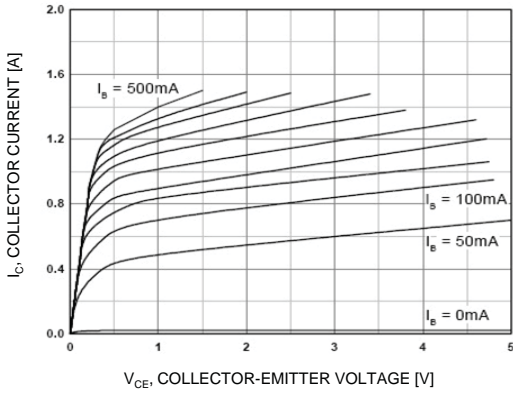


Figure 1. Static Characteristic

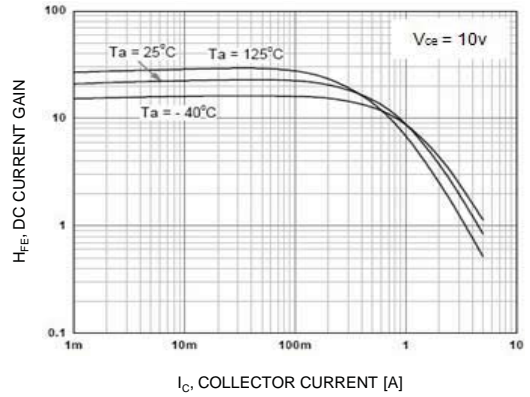


Figure 2. DC Current Gain

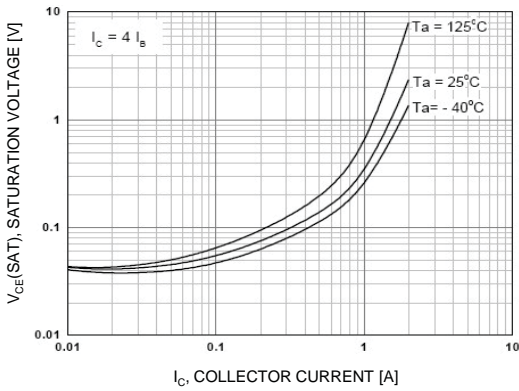


Figure 3. Collector-Emitter Saturation Voltage

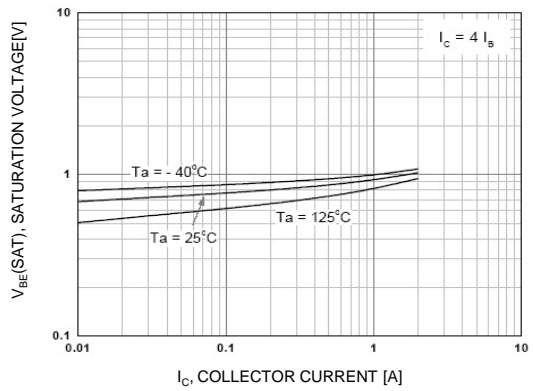


Figure 4. Base-Emitter Saturation Voltage

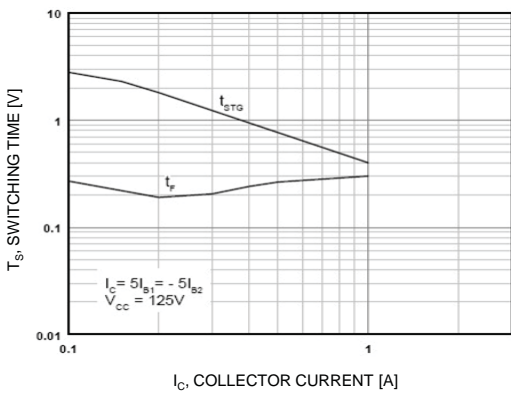


Figure 5. Resistive Load Switching Time

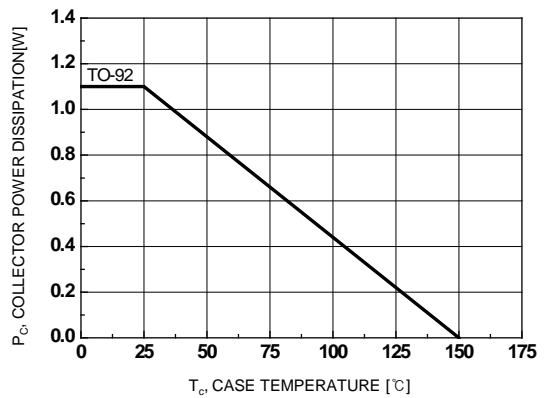


Figure 6. Power Derating

Typical Characteristics

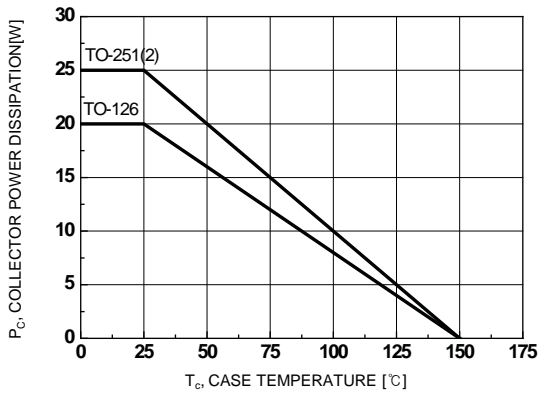
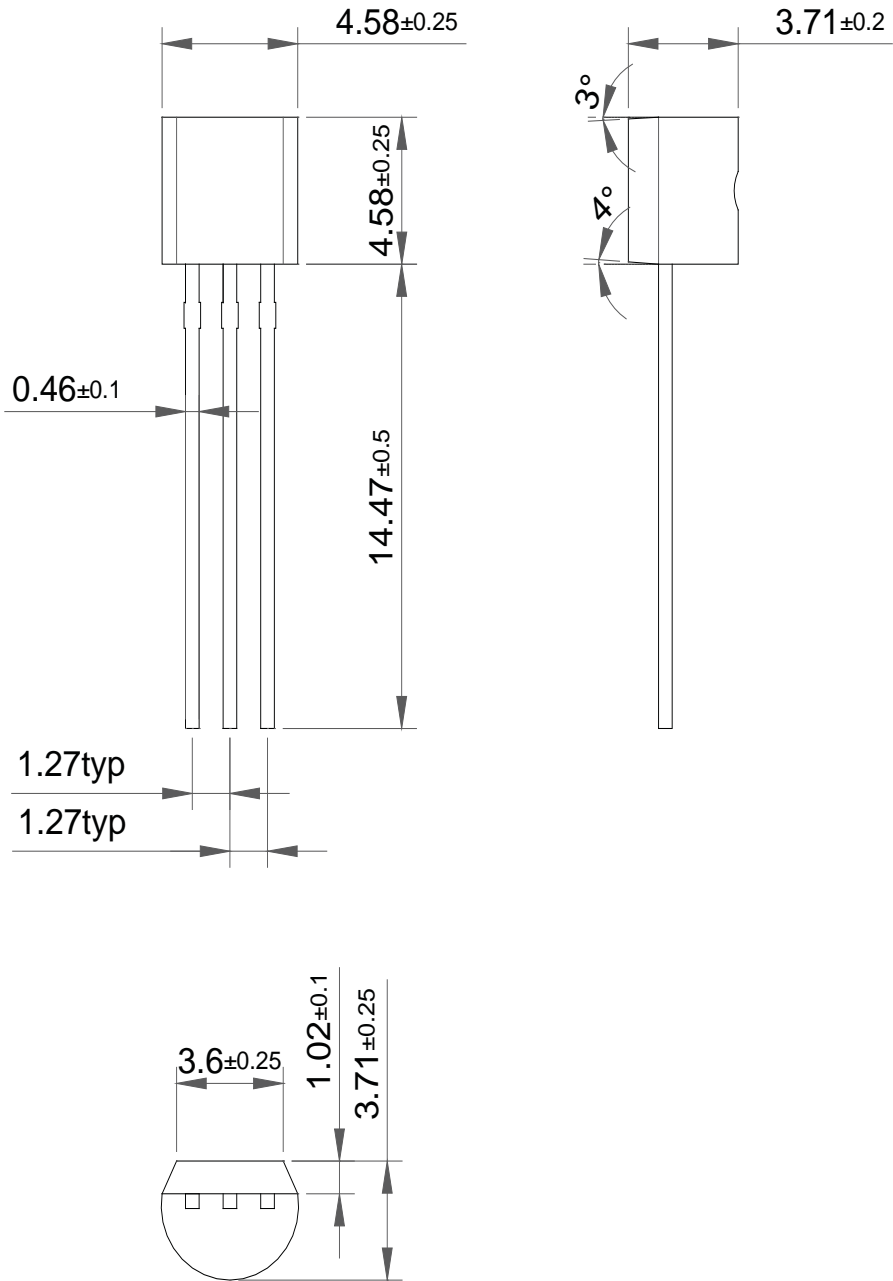


Figure 7. Power Derating

Package Dimension

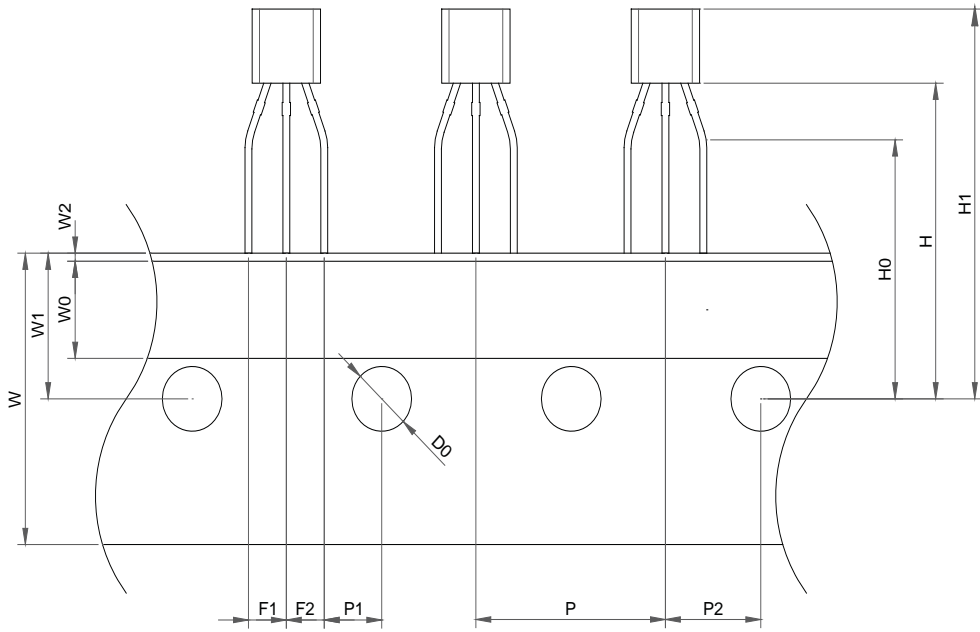
TO-92



Dimensions in Millimeters

Package Dimension

TO-92 TAPING

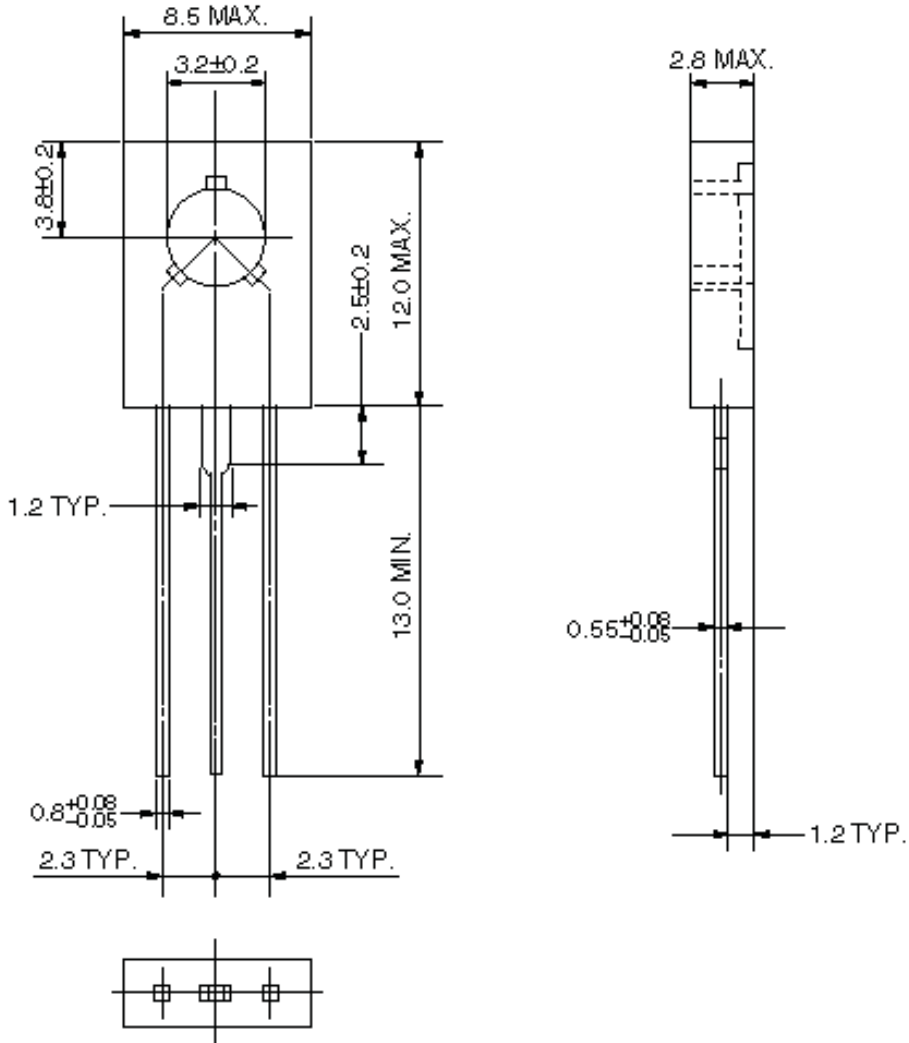


Item	Symbol	Dimension [mm]	
		Reference	Tolerance
Component pitch	P	12.7	±0.5
Side lead to center of feed hole	P1	3.85	±0.5
Center lead to center of feed hole	P2	6.35	±0.5
Lead pitch	F1,F2	2.5	+0.2/-0.1
Carrier Tape width	W	18.0	+1.0/-0.5
Adhesive tape width	W0	6.0	±0.5
Tape feed hole location	W1	9.0	±0.5
Adhesive tape position	W2	1.0 MAX	
Center of feed hole to bottom of component	H	19.5	±1
Center of feed hole to lead form	H0	16.0	±0.5
Component height	H1	27.0 max	
Tape feed hole diameter	D0	4.0	±0.2

Package Dimension

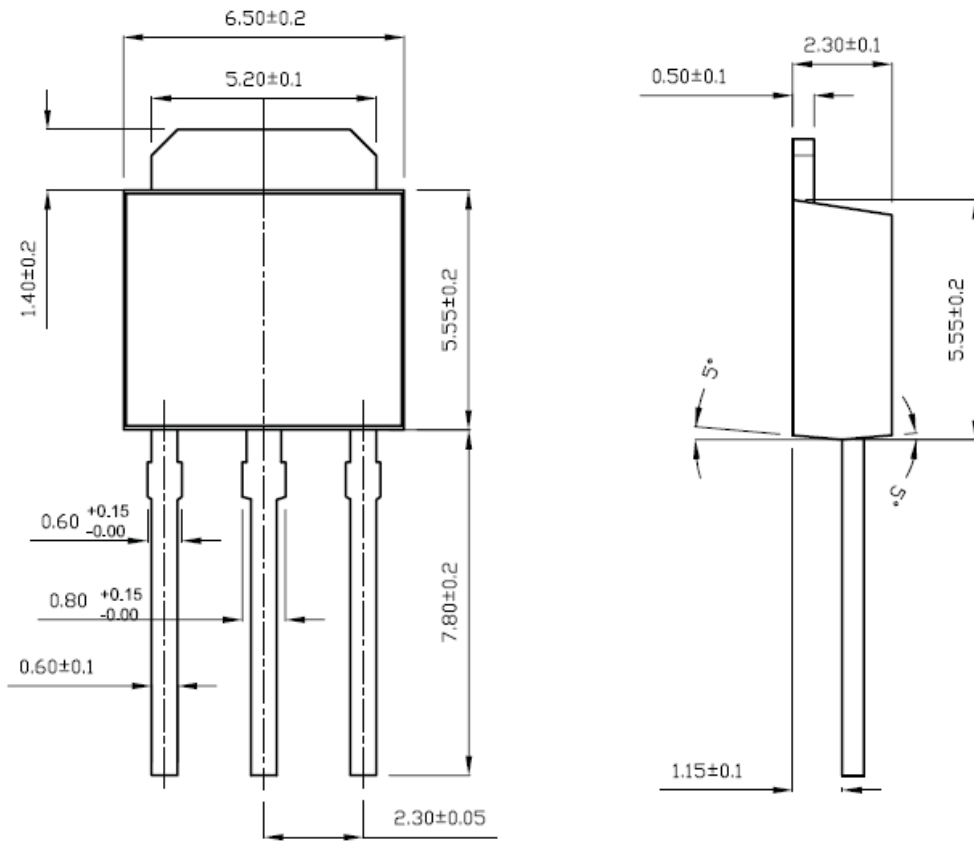
TO-126

UNIT : mm



Package Dimension

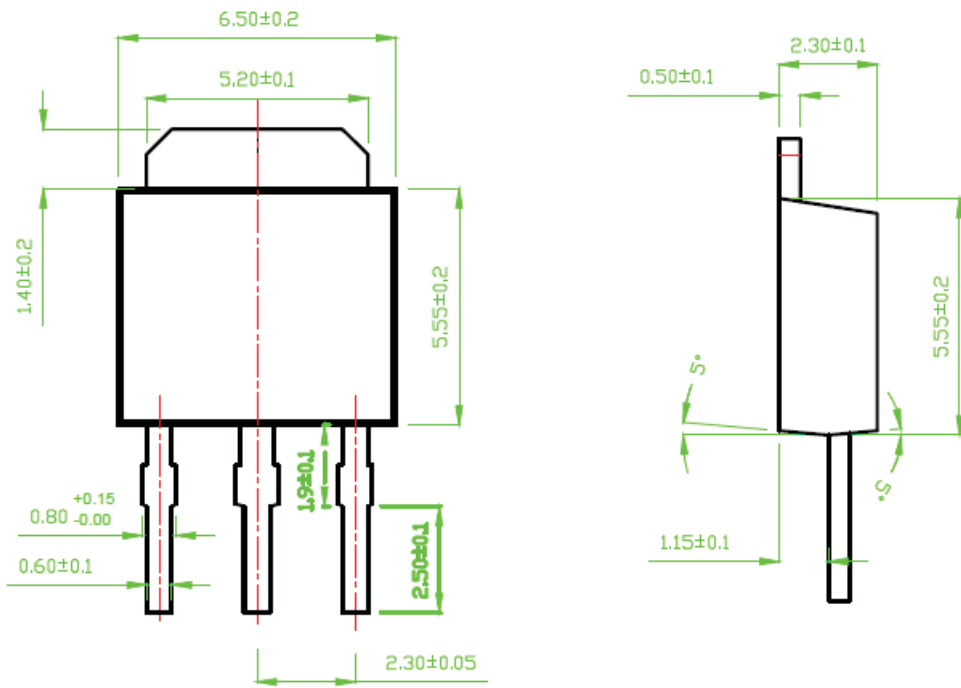
TO-251



Dimensions in Millimeters

Package Dimension

TO-251
Short Lead



Dimensions in Millimeters